

Device	Parameter	Units	Measured/ Extracted	Theoretical	% Error
[2a]	R_{sq}	Ω/\square	0.93	10	90.7
[2a]	N_D	cm^{-3}	10^{21}	10^{21}	0
[2b]	R_{sq}	Ω/\square	0.61	20	97.0
[17a]	Contact R_C	Ω	8.54	224	96.1
[17b]	Contact R_C	Ω	1.46	1760	99.9
[2c]	Resistance R	Ω	91.2	12500	99.3
[2c]	Contact R_C	Ω	10.88	224	95.1
[2d]	Resistance R	Ω	370	1970	81.2
[2d]	Contact R_C	Ω	51.45	1760	97.1
[3]	Field t_{OX}	nm	1150	477.2	141
[3]	Field V_T	V	N/A	N/A	N/A
[4]	Gate C_{FB}	F/cm ²	19.3×10^{-9}	3.99×10^{-8}	51.6
[4]	Gate C_{MIN}	F/cm ²	7.74×10^{-9}	N/A	N/A
[4]	Gate V_T	V	-0.26	0.03	767
[4]	Gate V_{FB}	V	5.5	-0.84	555
[4]	Gate t_{OX}	nm	88	86.5	1.73
[7]	Turn-on V	V	70	0.93	7430
[8]	ΔL	μm	0.453	3.76	88.0
[9]	ΔW	μm	-8.33	-2.76	202
[10]	V_T	V	-4.92	0.03	16300
[10]	Body effect γ	$\text{V}^{1/2}$	0.910	0.53	71.7
[10]	N_A	cm^{-3}	9.49×10^{24}	8×10^{14}	1.19×10^{12}
[10]	Low-field μ	$\text{cm}^2/(\text{V}\cdot\text{s})$?	?	?